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Vishay Siliconix

N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT	SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)
250	0.031 at V _{GS} = 10 V	63.5	57.6 nC
250	0.032 at V _{GS} = 7.5 V	62.5	37.0110



Ordering Information:

SUM10250E-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- ThunderFET® power MOSFET
- Tuned for the lowest R_{DS}-C_{oss} FOM
- Maximum 175 °C junction temperature
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



APPLICATIONS

- · Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- · Synchronous rectification
- DC/DC converter
- · Motor drive switch
- DC/AC inverter
- · Solar micro inverter

- N-Channel MOSFET
- Class D audio amplifier

ABSOLUTE MAXIMUM RATINGS (7	$\Gamma_{\rm C}$ = 25 °C, unless othe	rwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	250	.,
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current (T, I = 150 °C)	T _C = 25 °C		63.5	
Continuous Drain Current (1) = 150 °C)	T _C = 70 °C	I _D	36.6	^
Pulsed Drain Current (t = 100 μs)		I _{DM}	150	A
Avalanche Current L = 0.1 mH		I _{AS}	60	
Single Avalanche Energy ^a	L = U. I IIII	E _{AS}	180	mJ
Maximum Daway Discipation 3	T _C = 25 °C	В	375 ^b	W
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.4	C/VV

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	<u>'</u>		<u>'</u>	1		
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0 V, I _D = 250 μA	250	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA
		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	150	μA
		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	90	-	-	Α
Drain-Source On-State Resistance a	B-a/	V _{GS} = 10 V, I _D = 30 A	-	0.0247	0.0310	Ω
Diain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 30 \text{ A}$	-	0.0255	0.0320	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	63	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	3002	-	
Output Capacitance	Coss	V _{GS} = 0 V, V _{DS} = 125 V, f = 1 MHz	-	184	-	pF
Reverse Transfer Capacitance	C _{rss}		-	18	-	
Total Gate Charge ^c	Qg		-	57.6	88	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 125 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$	-	15.1	-	nC
Gate-Drain Charge ^c	Q_{gd}		-	18.4	-	
Gate Resistance	R_g	f = 1 MHz	1.5	3.1	5	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	13	26	
Rise Time ^c	t _r	$V_{DD} = 125 \text{ V}, R_L = 2.08 \Omega$	-	93	180	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 60$ A, V_{GEN} = 10 V, R_g = 1 Ω	-	30	60	
Fall Time ^c	t _f		-	72	144	
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 μs)	I _{SM}		-	-	100	Α
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.79	1.2	V
Reverse Recovery Time	t _{rr}		-	212	420	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	14.5	29	Α

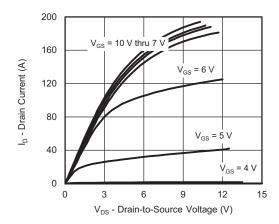
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

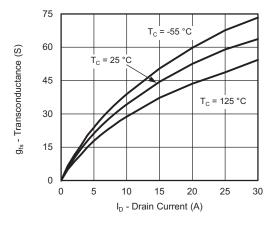
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



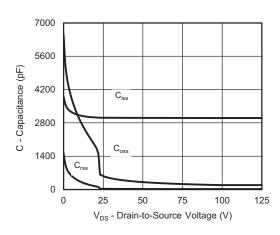
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



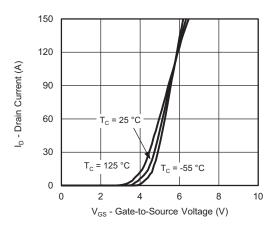
Output Characteristics



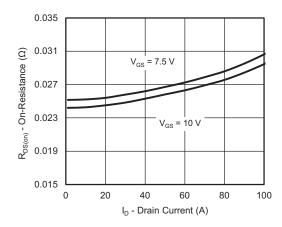
Transconductance



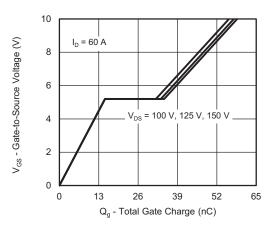
Capacitance



Transfer Characteristics



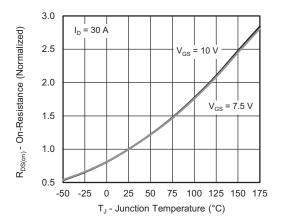
On-Resistance vs. Drain Current



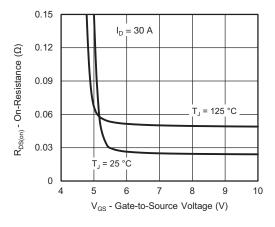
Gate Charge



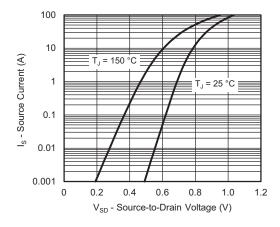
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



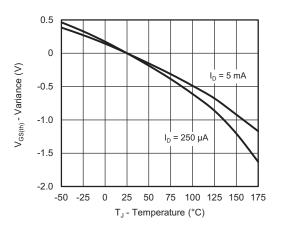
On-Resistance vs. Junction Temperature



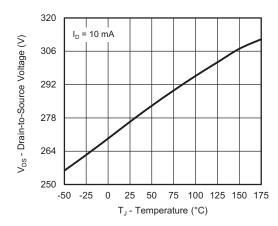
On-Resistance vs. Gate-to-Source Voltage



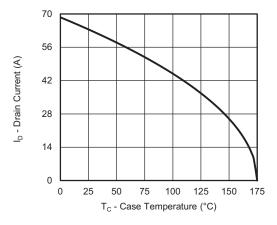
Source Drain Diode Forward Voltage



Threshold Voltage



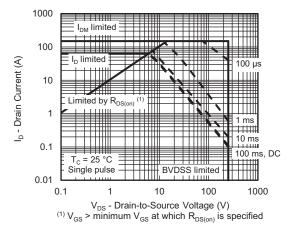
Drain Source Breakdown vs. Junction Temperature

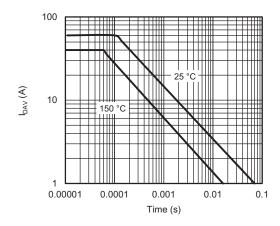


Current Derating



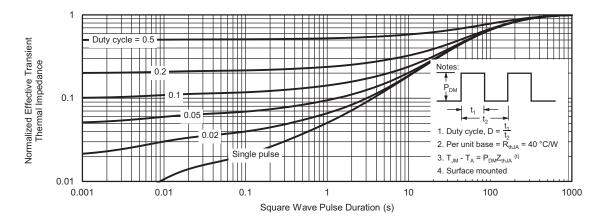
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)





Safe Operating Area

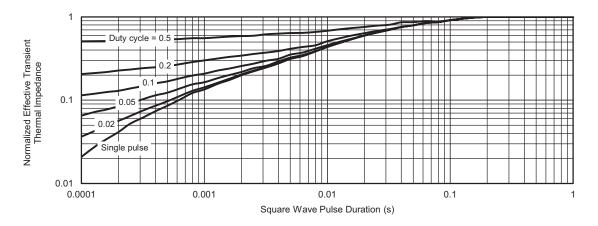
Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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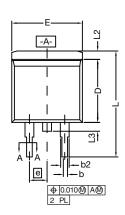
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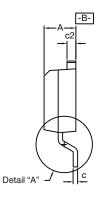


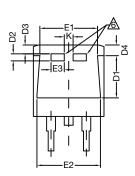
TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

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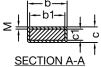








DETAIL A (ROTATED 90°)



<u>_</u>	b	ļ	<u> </u>
< T		c	ပ
SI	FCTION	1 A-A	Ŧ

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

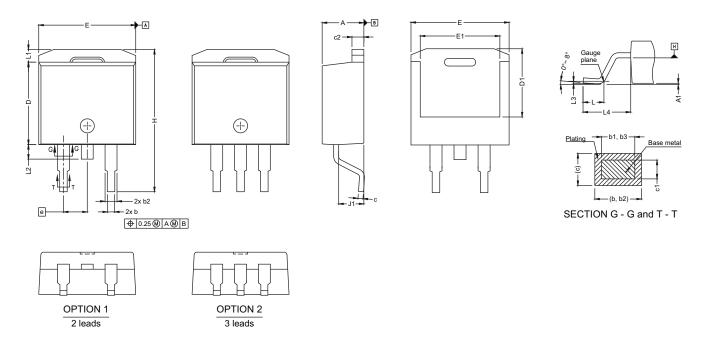
		INC	HES	MILLIN	METERS	
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.038 0.042		1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	<u>E1</u>	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54	BSC	
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		L1 0.090		2.286	2.794	
L2		0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010	BSC	0.254	BSC	
	М	_	0.002	-	0.050	



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VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5 10.55	
E	10.15		
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25	5 typ.	
L4	4.78 5.28		
J1	2.56	2.96	

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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